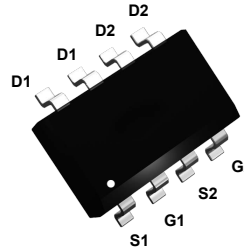
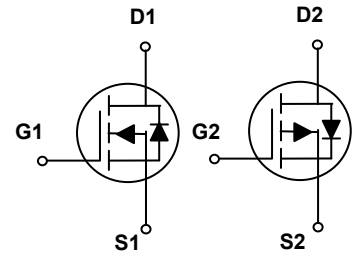


Main Product Characteristics

Channel	N-Channel	P-Channel
V_{DSS}	100V	-100V
$R_{DS(ON)(max.)}$	160m Ω	180m Ω
I_D	3A	-2.2A



SOP-8



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFQ1916 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating		Unit
Drain-Source Voltage	V_{DS}	100	-100	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Drain Current-Continuous ($T_C=25^\circ\text{C}$)	I_D	3.0	-2.2	A
Drain Current-Continuous ($T_C=100^\circ\text{C}$)		1.8	-1.4	A
Drain Current Pulsed ¹	I_{DM}	12	-8.8	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	2.3		W
Power Dissipation Derate above 25°C		0.02		W/ $^\circ\text{C}$
Max. Thermal Resistance Junction to Case	$R_{\theta JC}$	50.0		$^\circ\text{C}/\text{W}$
Max. Thermal Resistance Junction to Ambient	$R_{\theta JA}$	62.0		$^\circ\text{C}/\text{W}$
Storage Temperature Range	T_{STG}	-55 to +150		$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150		$^\circ\text{C}$

N-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100	-	-	V
BV _{DSS} Temperature Coefficient	ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =1mA	-	0.1	-	V/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V, T _J =25°C	-	-	1	μA
		V _{DS} =80V, V _{GS} =0V, T _J =125°C	-	-	10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2A	-	106	160	mΩ
		V _{GS} =4.5V, I _D =1A	-	110	180	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.1	-	2.9	V
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)}		-	-4	-	mV/°C
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =1A	-	2	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{2,3}	Q _g	V _{DS} =50V, I _D =2A, V _{GS} =10V	-	13.4	-	nC
Gate-Source Charge ^{2,3}	Q _{gs}		-	2.9	-	
Gate-Drain Charge ^{2,3}	Q _{gd}		-	1.7	-	
Turn-On Delay Time ^{2,3}	t _{d(on)}	V _{DD} =30V, R _G =3.3Ω, V _{GS} =10V, I _D =1A	-	1.7	-	nS
Rise Time ^{2,3}	t _r		-	6.7	-	
Turn-Off Delay Time ^{2,3}	t _{d(off)}		-	11.4	-	
Fall Time ^{2,3}	t _f		-	3.7	-	
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1MHz	-	821	-	pF
Output Capacitance	C _{oss}		-	35	-	
Reverse Transfer Capacitance	C _{rss}		-	20	-	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.3	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current	I _s	V _G =V _D =0V, Force Current	-	-	3	A
Pulsed Source Current	I _{SM}		-	-	12	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _s =1A, T _J =25°C	-	-	1	V

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

P-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-100	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	-	-	-1	μA
		V _{DS} =-80V, V _{GS} =0V, T _J =125°C	-	-	-10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-2A	-	150	180	mΩ
		V _{GS} =-4.5V, I _D =-1A	-	165	210	
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.6	-2.7	V
Forward Transconductance	g _{fs}	V _{DS} =-10V, I _D =-1.5A	-	6.5	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q _g	V _{DS} =-50V, I _D =-1A, V _{GS} =-10V	-	20	-	nC
Gate-Source Charge ^{3,4}	Q _{gs}		-	2.4	-	
Gate-Drain Charge ^{3,4}	Q _{gd}		-	3.3	-	
Turn-On Delay Time ^{3,4}	t _{d(on)}	V _{DD} =-50V, R _G =6Ω, V _{GS} =-10V, I _D =-1A	-	18	-	nS
Rise Time ^{3,4}	t _r		-	8	-	
Turn-Off Delay Time ^{3,4}	t _{d(off)}		-	100	-	
Fall Time ^{3,4}	t _f		-	30	-	
Input Capacitance	C _{iss}	V _{DS} =-50V, V _{GS} =0V, F=1MHz	-	1280	-	pF
Output Capacitance	C _{oss}		-	55	-	
Reverse Transfer Capacitance	C _{rss}		-	30	-	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	16	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current	I _S	V _G =V _D =0V, Force Current	-	-	-2.2	A
Pulsed Source Current	I _{SM}		-	-	-8.8	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1A, T _J =25°C	-	-	-1	V
Reverse Recovery Time	T _{rr}	V _R =-100V, I _S =-1A, di/dt=100A/μs, T _J =25°C	-	35	-	nS
Reverse Recovery Charge	Q _{rr}		-	30	-	nC

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=22A, starting T_J=25°C.
3. Pulse test: pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

N-Channel Typical Electrical and Thermal Characteristic Curves

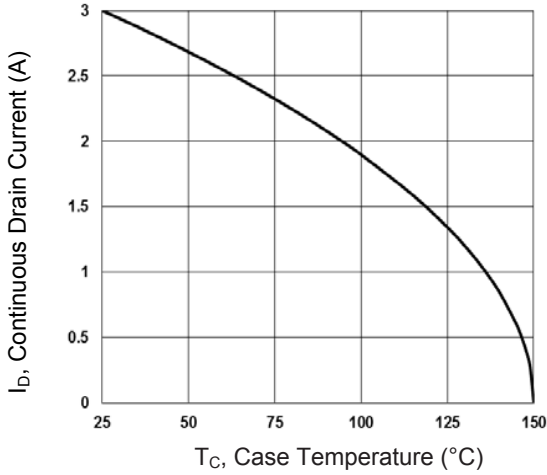


Figure 1. Continuous Drain Current vs. T_c

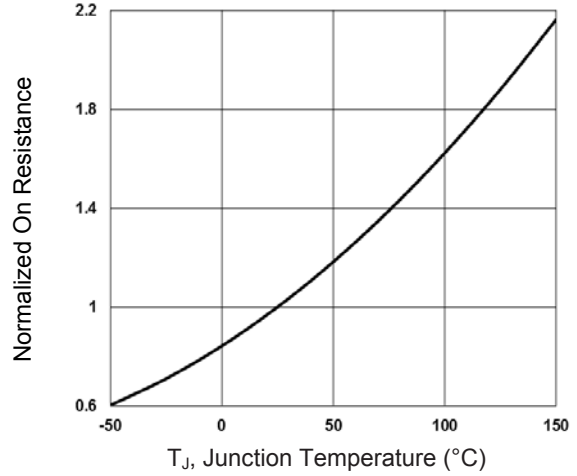


Figure 2. Normalized R_{DS(on)} vs. T_j

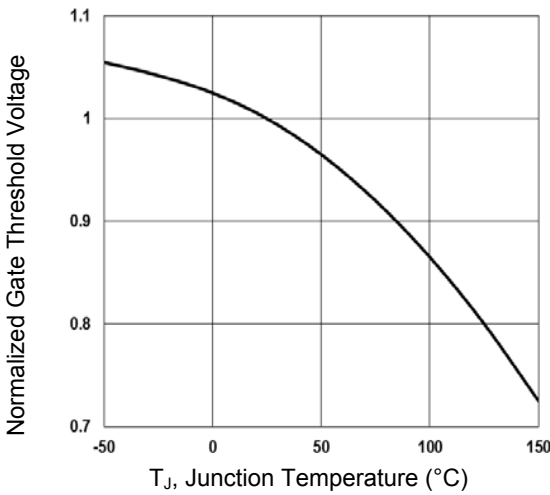


Figure 3. Normalized V_{th} vs. T_j

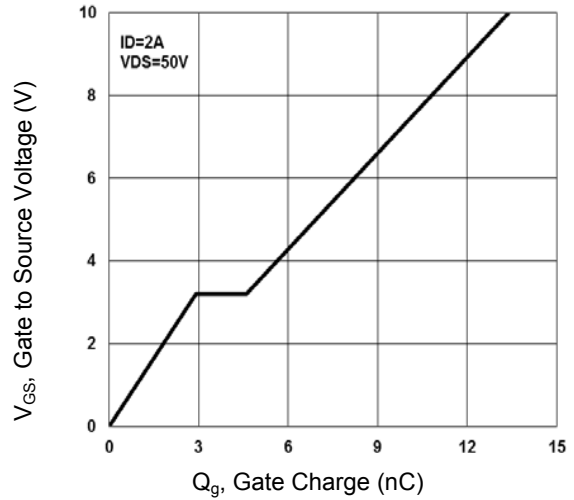


Figure 4. Gate Charge Waveform

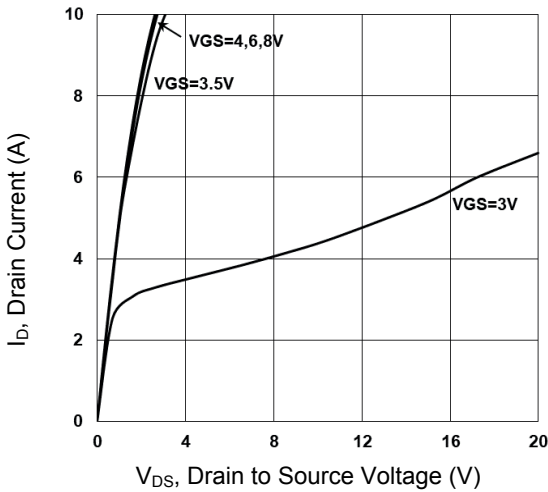


Figure 5. Typical Output Characteristics

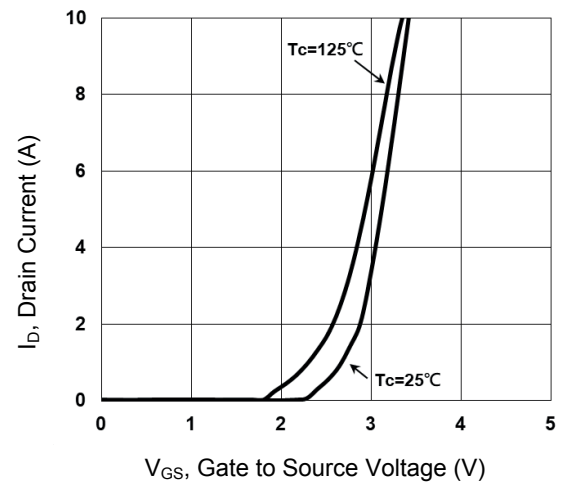


Figure 6. Transfer Characteristics

P-Channel Typical Electrical and Thermal Characteristic Curves

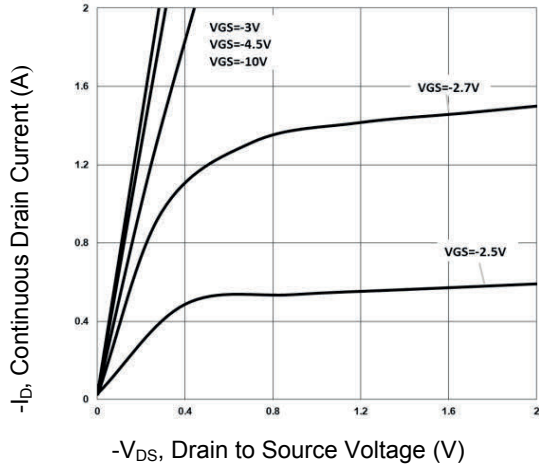


Figure 1. Typical Output Characteristics

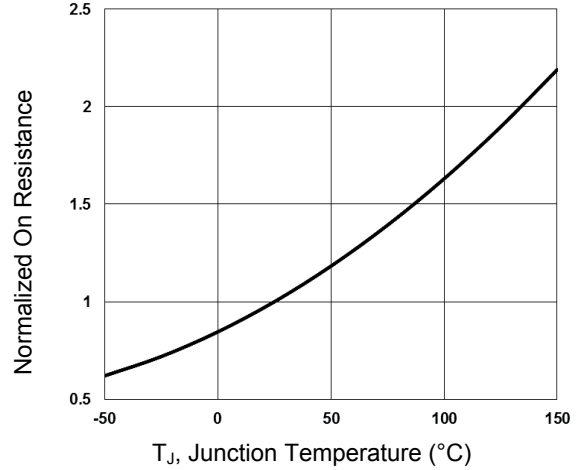


Figure 2. Normalized $R_{DS(ON)}$ vs. T_J

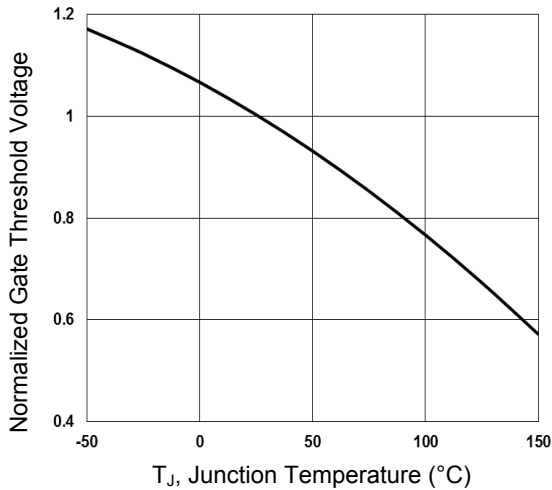


Figure 3. Normalized V_{th} vs. T_J

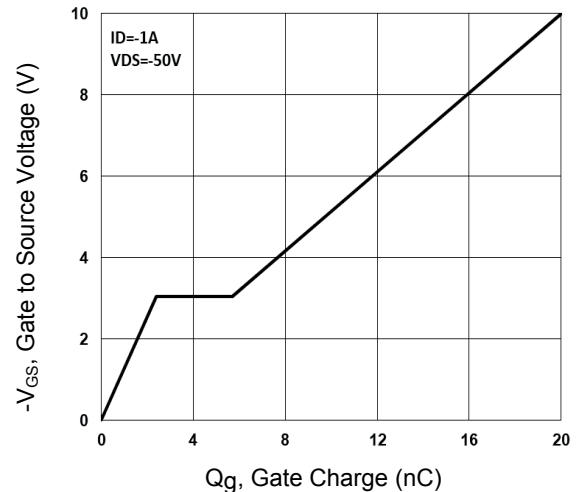


Figure 4. Gate Charge Characteristics

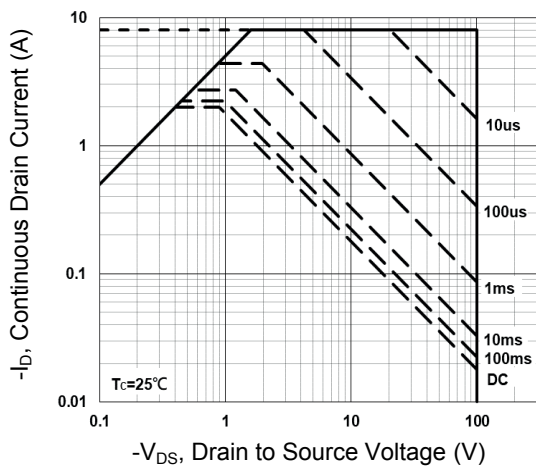


Figure 5. Maximum Safe Operation Area

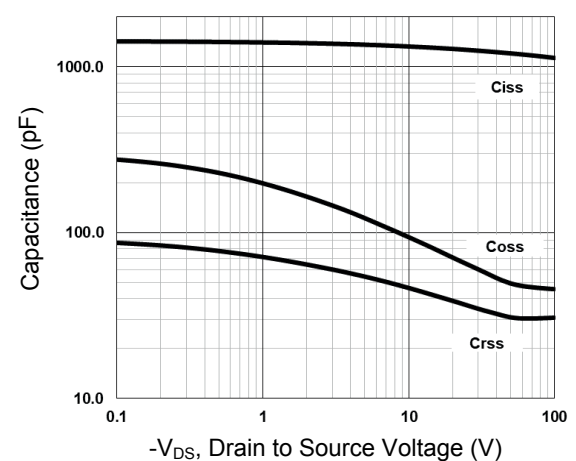
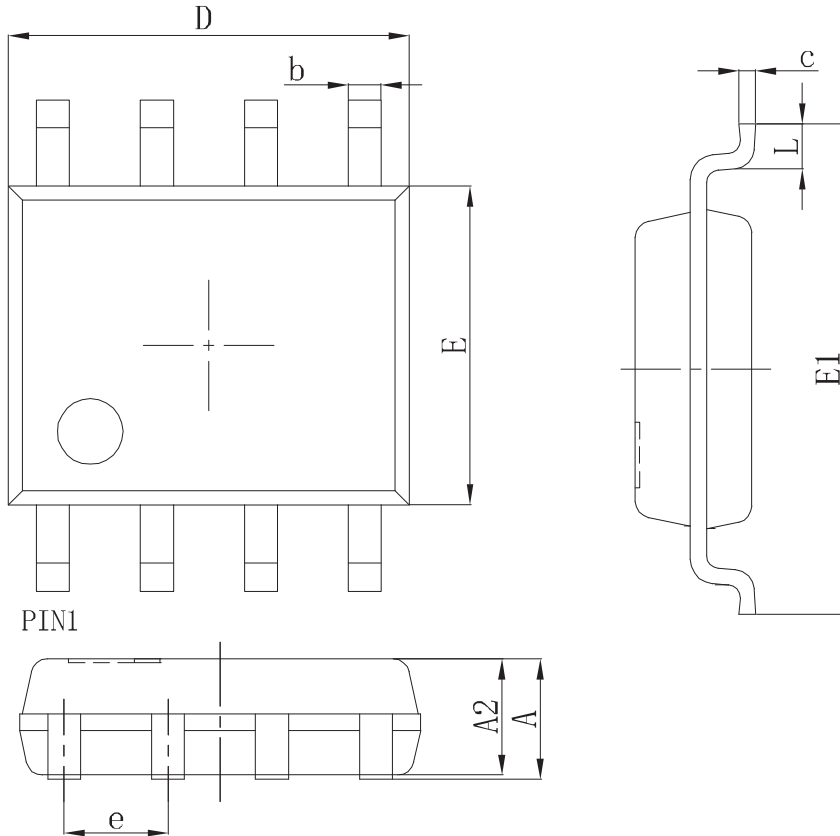


Figure 6. Capacitance Characteristics

Package Outline Dimensions (SOP-8)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.30	1.70	0.051	0.067
A2	1.25	1.55	0.049	0.061
c	0.17	0.25	0.007	0.010
E	3.80	4.00	0.150	0.157
E1	5.80	6.20	0.228	0.244
L	0.45	0.75	0.018	0.030
b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197
e	1.27 BSC		0.050 BSC	

Order Information

Device	Package	Marking	Carrier	Quantity
GSFQ1916	SOP-8	Q1916	Tape & Reel	3,000 Pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com